

5

3. The composite field effect transistor of claim 2, wherein the metal-oxide-semiconductor field effect transistor comprises an enhancement mode metal-oxide-semiconductor field effect transistor.

4. The composite field effect transistor of claim 3, wherein the enhancement mode metal-oxide-semiconductor field effect transistor comprises an n-channel enhancement mode metal-oxide-semiconductor field effect transistor.

5. The composite field effect transistor of claim 1, wherein the metal-oxide-semiconductor field effect transistor comprises an enhancement mode metal-oxide-semiconductor field effect transistor.

6. The composite field effect transistor of claim 1, wherein the gate of the metal-oxide-semiconductor field effect transistor and the cathode of the zener diode are coupled to an input impedance.

7. The composite field effect transistor of claim 6, wherein the input impedance comprises a capacitive element.

8. The composite field effect transistor of claim 6, wherein the input impedance comprises a resistive element.

9. The composite field effect transistor of claim 6, wherein the input impedance comprises:

- a capacitive element; and
- a resistive element coupled in parallel with the capacitive element.

10. The composite field effect transistor of claim 1, wherein the gate of the metal-oxide-semiconductor field effect transistor is further coupled to a drive signal.

11. A composite field effect transistor comprising:

- a zener diode;
- a depletion mode junction field effect transistor having a gate coupled to an anode of the zener diode;
- a metal-oxide-semiconductor field effect transistor having a drain coupled to a source of the depletion mode junction field effect transistor and having a gate coupled to a cathode of the zener diode and a drive signal.

12. The composite field effect transistor of claim 11, wherein the metal-oxide-semiconductor field effect transistor comprises an enhancement mode metal-oxide-semiconductor field effect transistor.

13. The composite field effect transistor of claim 12, wherein the enhancement mode metal-oxide-semiconductor field effect transistor comprises an n-channel enhancement mode metal-oxide-semiconductor field effect transistor.

14. The composite field effect transistor of claim 13, wherein the gate of the metal-oxide-semiconductor field effect transistor and the cathode of the zener diode is coupled to an input impedance.

6

15. The composite field effect transistor of claim 14, wherein the input impedance comprises:

- a capacitive element; and
- a resistive element coupled in parallel with the capacitive element.

16. The composite field effect transistor of claim 14, wherein a drain of the junction field effect transistor is coupled to a load impedance.

17. A composite field effect transistor comprising:

- a zener diode;
- a depletion mode junction field effect transistor, wherein a drain of the depletion mode junction field effect transistor is coupled to a drain of the composite field effect transistor and wherein a gate of the depletion mode junction field effect transistor is coupled to an anode of the zener diode; and

an enhancement mode metal-oxide-semiconductor field effect transistor, wherein a drain of the enhancement mode metal-oxide-semiconductor field effect transistor is coupled to a source of the depletion mode junction field effect transistor, wherein a gate of the enhancement mode metal-oxide-semiconductor field effect transistor is coupled to a cathode of the zener diode and a gate of the composite field effect transistor, and wherein a source of the enhancement mode metal-oxide-semiconductor field effect transistor is coupled to a source of the composite field effect transistor.

18. The composite field effect transistor of claim 17, wherein the zener diode causes the enhancement mode metal-oxide-semiconductor field effect transistor to become fully enhanced before the gate of the depletion mode junction field effect transistor is clamped by a gate-to-source potential of the depletion mode junction field effect transistor, as the source of the depletion mode junction field effect transistor is pulled down.

19. The composite field effect transistor of claim 17, wherein the zener diode provides a bi-directional impedance path to charge and discharge a parasitic capacitance of the depletion mode junction field effect transistor.

20. The composite field effect transistor of claim 17, wherein the zener diode clamps a potential at the gate of the enhancement mode metal-oxide-semiconductor field effect transistor.

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